
10-bit 1-channel 50/100 MSPS ADC

SPECIFICATION

1. FEATURES

- TSMC CMOS 65 nm
- Resolution 10 bit
- 1 channel
- Different power supplies for digital (1.2 V) and analog parts (1.2 V)
- Sampling rate up to 100 MSPS
- Stand-by mode (current consumption 10 uA)
- Low-power dissipation:
 - 34 mW at 100 MSPS
 - 21 mW at 50 MSPS
- Differential full-scale input range peak-to-peak 1 V
- Dynamic performance:
 - 66.0 dB SFDR, 54.2 dB SINAD at 50 MSPS and $f_{in} = 10.7$ MHz
 - 66.3 dB SFDR, 53.0 dB SINAD at 100 MSPS and $f_{in} = 10.7$ MHz
- Differential nonlinearity ± 0.79 LSB
- Integral nonlinearity ± 0.94 LSB
- Compact die area 0.26 mm^2
- Portable to other technologies (upon request)

2. APPLICATION

- WiFi, WiMax
- Mobile Communications
- High quality imaging video systems
- Data acquisition systems
- Portable ultrasound and digital beam-forming systems

3. OVERVIEW

The 10-bit 50/100 MSPS ADC employs a high-performance front-end sample-and-hold with differential multistage pipelined architecture and output error correction logic. The biasing circuit and the clock generator are also included to provide a complete ADC. The ADC operates with sampling rate up to 100 MSPS and a corresponding input clock up to 200 MHz (input clock is divided by two). The ADC can be configured to achieve addition power saving at low sampling rate, supports stand-by mode and features the excellent dynamic and static performance, wide bandwidth inputs, low power consumption and compact die area.

The block is designed on TSMC CMOS 65 nm technology.

4. STRUCTURE

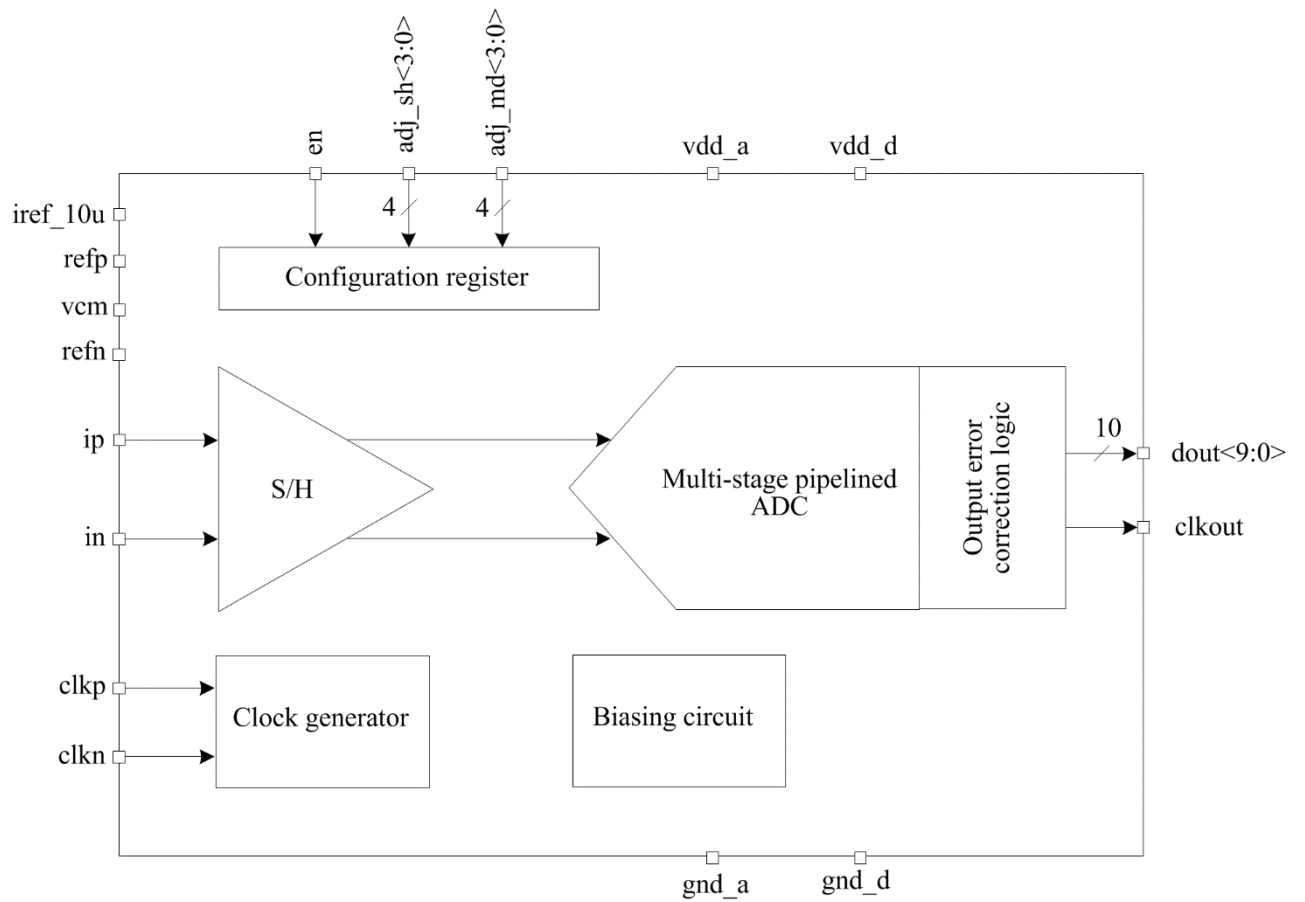


Figure 1: 10-bit 50/100 MSPS ADC structure

5. PIN DESCRIPTION

Name	Direction	Description
iref_10u	I	Reference current (10 uA)
ip	I	Analog differential input (1 V peak-to-peak)
in		
clkp	I	200 MHz differential clock input
clkn		
refp	I	Positive reference voltage (0.8 V)
vcm	I	Common mode voltage (0.55 V)
refn	I	Negative reference voltage (0.3 V)
en	I	ADC enable: “0” disabled “1” enabled
adj_sh<3:0>	I	Register of adjust reference current the sample and hold: “0000” unused “0001” 5 uA ... with step of 5 uA “1111” 75 uA
adj_md<3:0>	I	Register of adjust reference current the multi-stage ADC: “0000” unused “0001” 5 uA ... with step of 5 uA “1111” 75 uA
dout<9:0>	O	Output data
clkout	O	100 MHz output clock
vdd_a	I/O	Analog block supply voltage (1.2 V)
vdd_d	I/O	Digital blocks supply voltage (1.2 V)
gnd_a	I/O	Analog blocks ground
gnd_d	I/O	Digital blocks ground

6. FUNCTIONAL DESCRIPTION

The input clock is divided by two and after t_{d1} time analog input voltage is sampled by the positive edge. The output data after the conversion latency of 8 clock cycles is latched.

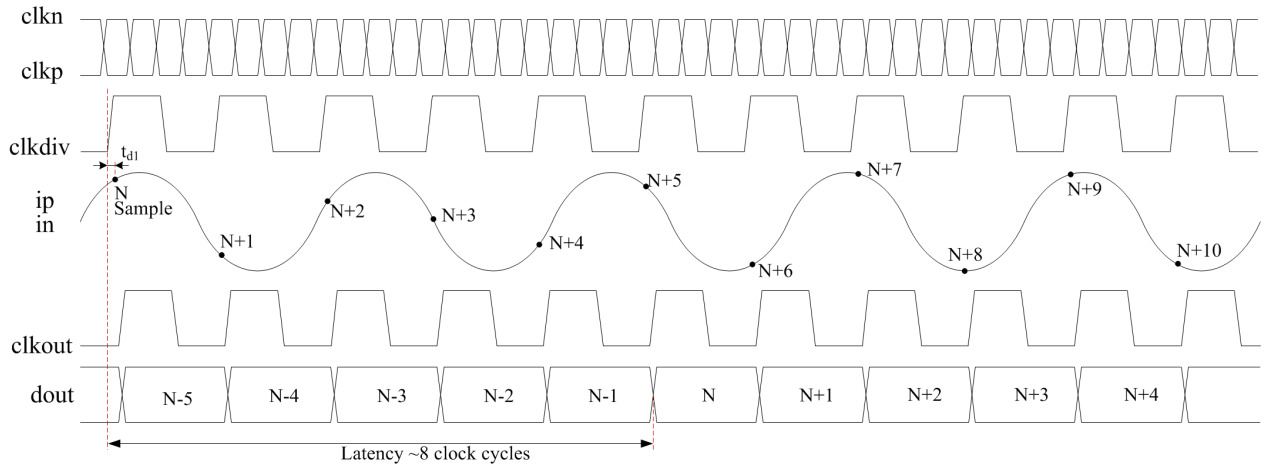


Figure 2: Timing diagram for normal operation

7. CURRENT CONSUMPTION PROGRAMMABILITY

There is also ability to adjust reference current the sample-and-hold and multi-stage pipeline ADC. The values of reference current determine current consumption. Adjustable reference current allows configuring operation mode related to static, dynamic performance and sampling rate.

$$I_{DC} = 5 \text{ uA} \cdot 440 \cdot \text{adj_sh} + 5 \text{ uA} \cdot 440 \cdot \text{adj_md},$$

where **adj_sh** – decimal representation register of adjust reference current the sample and hold;
adj_md – decimal representation register of adjust reference current the multi-stage pipeline ADC.

8. LAYOUT DESCRIPTION

8.1 TECHNOLOGY OPTIONS

ADC is designed under TSMC 65 nm LP CMOS technology process with following options:

- 4x1z1u metal option
- 1.2 V standard Vt MOS
- 1.2 V low Vt MOS
- 2.0 fF/um² MIM capacitor
- P+polysilicon OP resistor

8.2 PHYSICAL DIMENTIONS

ADC layout dimensions are given in the table 1.

Table 1: Block dimension.

Dimension	Value	Unit
Height	410	um
Width	630	um

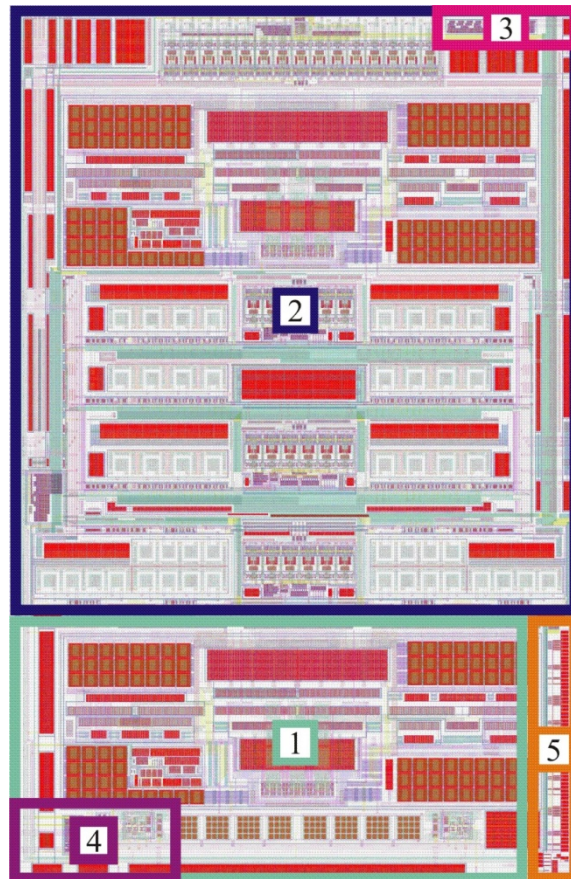


Figure 3: ADC layout

1. Sample and hold
2. Multistage ADC
3. Output error correction logic
4. Clock generator
5. Biasing circuit

9. INTEGRATION GUIDELINES

9.1 PLACE AND ROUTE GUIDELINES

- 1) ADC analog inputs `ip` and `in` signals should be connected to analog IO PADs or an internal analog circuits (intermediate frequency amplifier, filter). IO PADs should not have an internal resistor to increase bandwidth.
- 2) Wiring of analog inputs should be symmetrical and as short as possible.
- 3) Noisy, power and high-frequency circuits should not place near ADC.
- 4) Minimum space 40 μm between ADC and other circuits should be kept.
- 5) Minimum metal wiring width is 50 μm for `vdd_a` and `gnd_a`. Multiple layers of metal can be used to reduce layout space.
- 6) Minimum metal wiring width is 10 μm for `vdd_d` and `gnd_d`. Multiple layers of metal can be used to reduce layout space.
- 7) Allowable total resistance of `vdd_a` and `gnd_a` are 0.5 Ohm. Blocking capacitors should be added and placed as close as possible.
- 8) Allowable total resistance of `vdd_a` and `gnd_a` are 2 Ohm. Blocking capacitors should be added and placed as close as possible.

10. OPERATING CHARACTERISTICS

10.1 TECHNICAL CHARACTERISTICS

Technology _____ TSMC CMOS 65 nm
 Status _____ silicon proven
 Area _____ 0.26 mm²

10.2 ELECTRICAL CHARACTERISTICS

The values of electrical characteristics are specified for $V_{dd_a}=1.14\div1.26$ V, $V_{dd_d}=1.14\div1.26$ V and $T_j=-40\div+85^{\circ}\text{C}$, typical values are at $V_{dd_a}=1.2$ V, $V_{dd_d}=1.2$ V, $T_j=+27^{\circ}\text{C}$, unless otherwise noted.

Parameter	Symbol	Conditions	Value			Unit
			min	typ.	max	
Operating temperature range	T _j	-	-40	27	+85	°C
Power Supply Requirements						
Analog supply voltage	V _{dd_a}	-	1.14	1.2	1.26	V
Digital supply voltage	V _{dd_d}	-	1.14	1.2	1.26	V
Current consumption in normal mode	I _{cn}	F _S = 50 MSPS	-	17	-	mA
		F _S = 100 MSPS	-	28	-	mA
Current consumption in stand-by mode	I _s	-	-	10	-	uA
Power consumption in normal mode	P _{cn}	F _S = 50 MSPS	-	21	-	mW
		F _S = 100 MSPS	-	34	-	mW
DC Accuracy						
Resolution	N	-	-	10	-	bit
Differential nonlinearity	DNL	F _S = 50 MSPS	-	±0.79	-	LSB
Integral nonlinearity	INL	F _S = 50 MSPS	-	±0.94	-	LSB
Offset error	OE	F _S = 50 MSPS	-	±2.0	-	LSB
Gain error	GE	F _S = 50 MSPS	-	±0.11	-	LSB
Analog Inputs						
Differential full-scale input range	A _{IN p-p}	-	-	1	-	V
Input common-mode voltage	V _{cm_in}	-	0.5	-	0.55	V
Input capacitance	C _{eff_in}	-	-	4	-	pF
Input resistance	R _{eff_in}	-	-	100	-	kOhm
Digital Inputs and Outputs						
Output logic coding	-	-	Offset binary			code
Input logic-level high	V _{IH}	-	0.7 V _{dd_d}	-	-	V
Input logic-level low	V _{IL}	-	-	-	0.3 V _{dd_d}	V
Timing Information						
Input clock	F _{clk}	-	-	-	200	MHz
Sampling rate	F _s	F _{clk} /2	10	-	100	MSPS
Duty cycle	S	-	45	50	55	%
Latency	L	-	-	8	-	clock cycles
External Reference Requirements						
Reference current	I _{ref}	-	9.9	10	10.1	uA
Positive reference voltage	V _{refp}	-	-	0.80	-	V
Common mode voltage	V _{cm}	-	-	0.55	-	V
Negative reference voltage	V _{refn}	-	-	0.30	-	V

Table “Electrical characteristics” (continue)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Dynamic characteristic at F _S = 50 MSPS						
Input frequency range	f _{in}	-	0	-	530	MHz
Signal-to-noise ratio	SNR	f _{in} = 10.7 MHz	-	54.3	-	dB
		f _{in} = 21.4 MHz	-	53.5	-	
		f _{in} = 30 MHz	-	53.0	-	
		f _{in} = 70 MHz	-	49.8	-	
Signal-to-noise and distortion ratio	SINAD	f _{in} = 10.7 MHz	-	54.2	-	dB
		f _{in} = 21.4 MHz	-	53.4	-	
		f _{in} = 30 MHz	-	52.9	-	
		f _{in} = 70 MHz	-	49.6	-	
Effective number of bits	ENOB	f _{in} = 10.7 MHz	-	8.7	-	bits
		f _{in} = 21.4 MHz	-	8.6	-	
		f _{in} = 30 MHz	-	8.5	-	
		f _{in} = 70 MHz	-	8.0	-	
Worst second or third harmonic	-	f _{in} = 10.7 MHz	-	78	-	dB
		f _{in} = 21.4 MHz	-	81	-	
		f _{in} = 30 MHz	-	67	-	
		f _{in} = 70 MHz	-	76	-	
Spurious-free dynamic range	SFDR	f _{in} = 10.7 MHz (see Fig. 18)	-	64	-	dB
		f _{in} = 21.4 MHz (see Fig. 20)	-	61	-	
		f _{in} = 30 MHz (see Fig. 22)	-	58	-	
		f _{in} = 70 MHz	-	54.5	-	
Two-tone spurious-free-dynamic range	Two-tone SFDR	f _{in} = 10.7 MHz	-	64	-	dB
		f _{in} = 21.4 MHz	-	61	-	
		f _{in} = 30 MHz	-	58	-	
Intermodulation distortion third-order	IMD3	f _{in} = 10.7 MHz (see Fig. 19)	-	74	-	dB
		f _{in} = 21.4 MHz (see Fig. 21)	-	76	-	
		f _{in} = 30 MHz (see Fig. 23)	-	71	-	
Full power bandwidth	F _B	-	-	560	-	MHz
Dynamic characteristic at F _S = 100 MSPS						
Input frequency range	f _{in}	-	0	-	530	MHz
Signal-to-noise ratio	SNR	f _{in} = 10.7 MHz	-	53.1	-	dB
		f _{in} = 21.4 MHz	-	52.4	-	
		f _{in} = 30 MHz	-	52.0	-	
		f _{in} = 70 MHz	-	48.7	-	
Signal-to-noise and distortion ratio	SINAD	f _{in} = 10.7 MHz	-	53.0	-	dB
		f _{in} = 21.4 MHz	-	52.2	-	
		f _{in} = 30 MHz	-	51.8	-	
		f _{in} = 70 MHz	-	48.5	-	
Effective number of bits	ENOB	f _{in} = 10.7 MHz	-	8.5	-	bit
		f _{in} = 21.4 MHz	-	8.4	-	
		f _{in} = 30 MHz	-	8.3	-	
		f _{in} = 70 MHz	-	7.8	-	
Worst second or third harmonic	-	f _{in} = 10.7 MHz	-	72	-	dB
		f _{in} = 21.4 MHz	-	67	-	
		f _{in} = 30 MHz	-	67	-	
		f _{in} = 70 MHz	-	59	-	
Spurious-free dynamic range	SFDR	f _{in} = 10.7 MHz	-	66.3	-	dB
		f _{in} = 21.4 MHz	-	63.7	-	
		f _{in} = 30 MHz	-	60.5	-	
		f _{in} = 70 MHz	-	52.1	-	
Full power bandwidth	F _R	-	-	400	-	MHz

11. TYPICAL CHARACTERISTICS

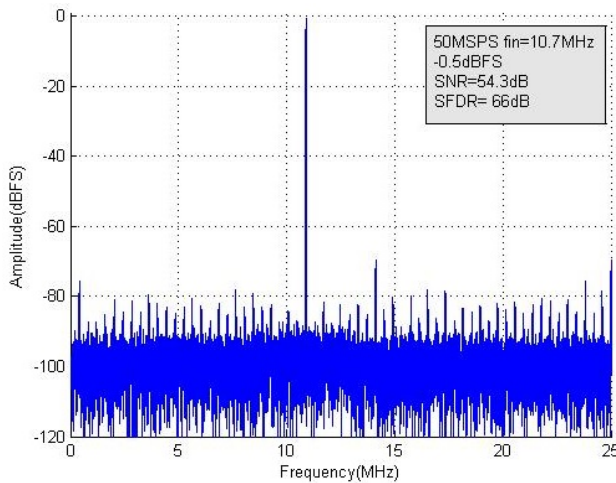


Figure 4: Spectrum with $F_S=50$ MSPS and $f_{in}=10.7$ MHz

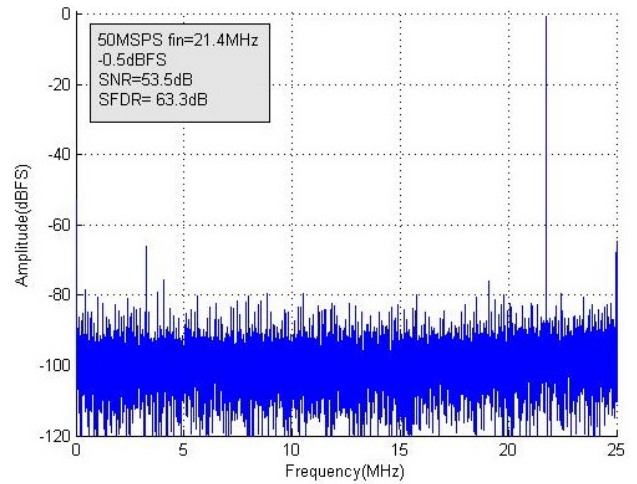


Figure 5: Spectrum with $F_S=50$ MSPS and $f_{in}=21.4$ MHz

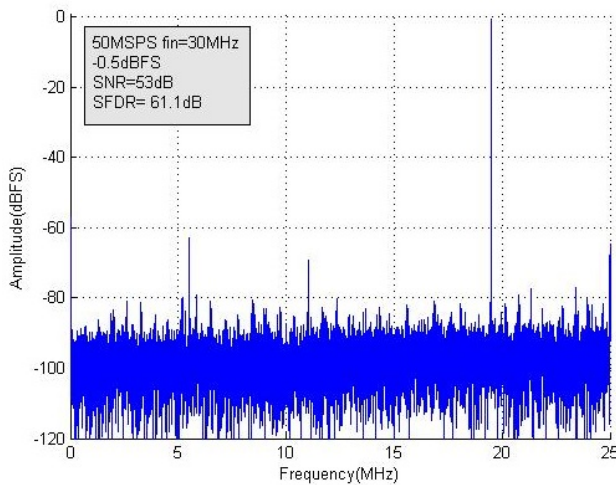


Figure 6: Spectrum with $F_S=50$ MSPS and $f_{in}=30$ MHz

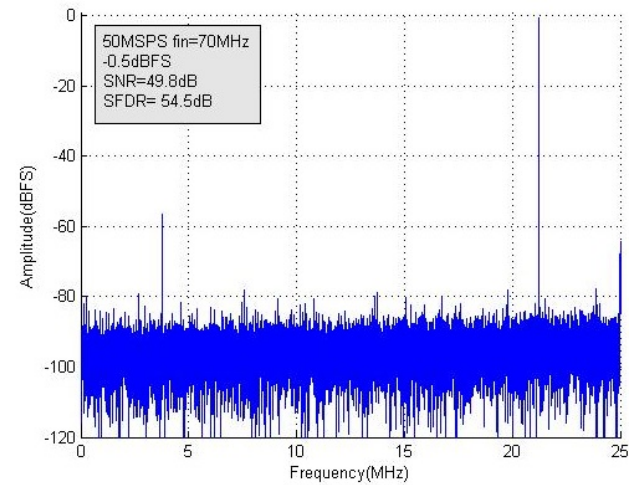


Figure 7: Spectrum with $F_S=50$ MSPS and $f_{in}=70$ MHz

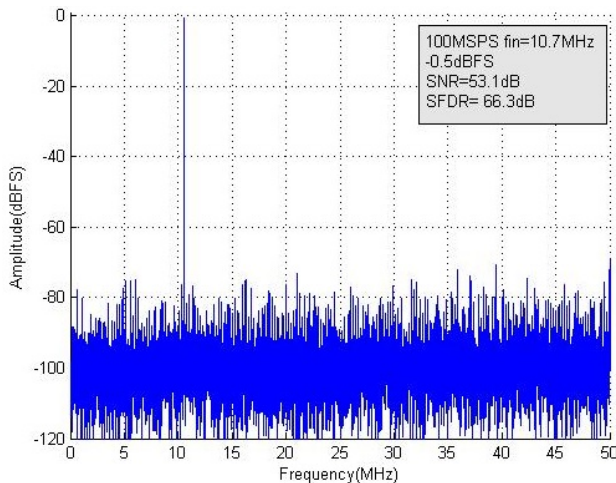


Figure 8: Spectrum with $F_S=100$ MSPS and $f_{in}=10.7$ MHz

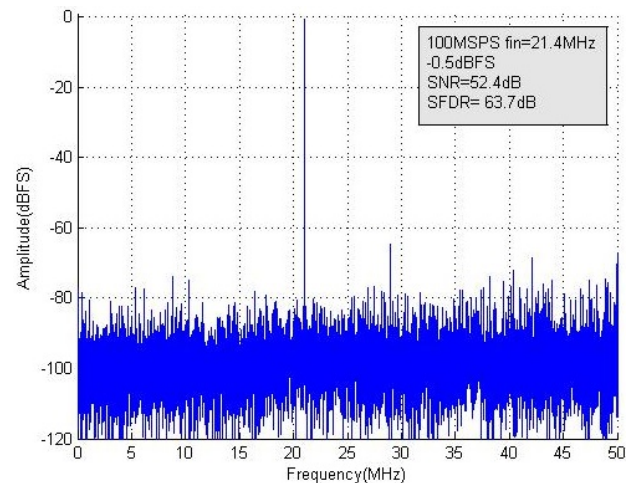


Figure 9: Spectrum with $F_S=100$ MSPS and $f_{in}=21.4$ MHz

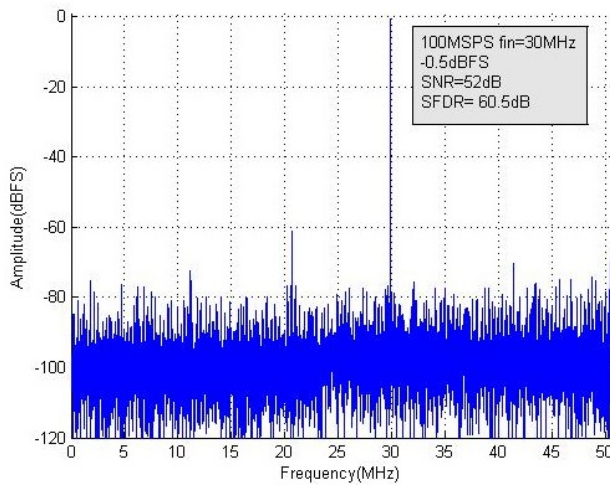


Figure 10: Spectrum with $F_S= 100$ MSPS and $f_{in}= 30$ MHz

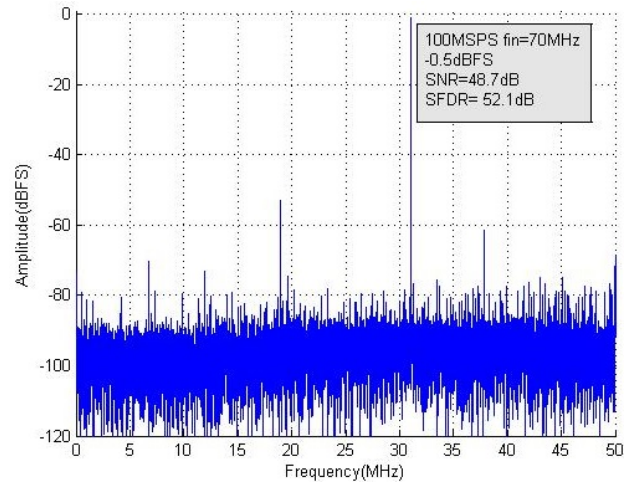


Figure 11: Spectrum with $F_S= 100$ MSPS and $f_{in}= 70$ MHz

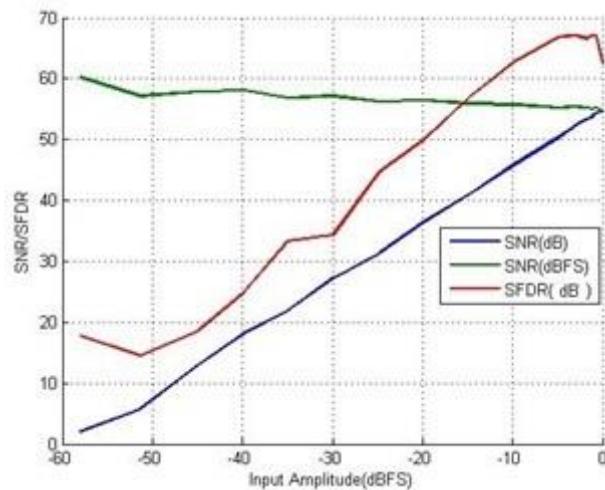


Figure 12: SNR/SFDR vs. input amplitude with $F_S= 50$ MSPS and $f_{in}= 10.7$ MHz

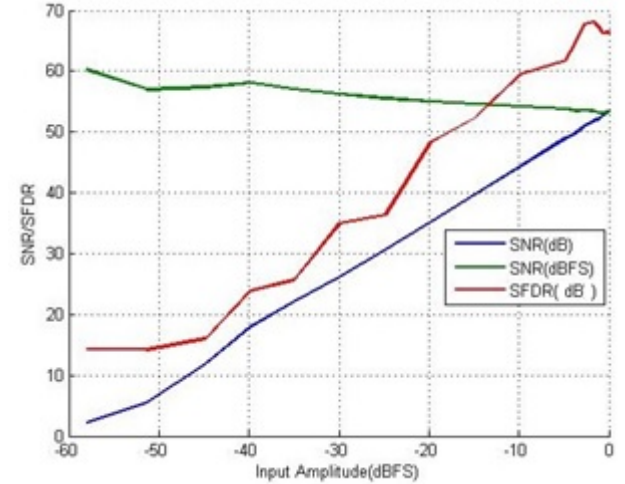


Figure 13: SNR/SFDR vs. input amplitude with $F_S= 100$ MSPS and $f_{in}= 10.7$ MHz

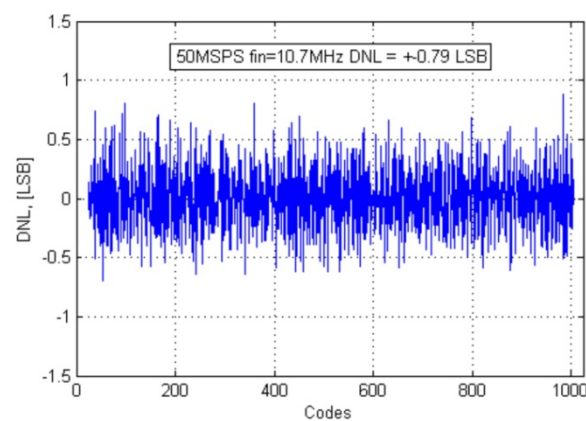


Figure 14: DNL with $F_S= 50$ MSPS and $f_{in}= 10.7$ MHz

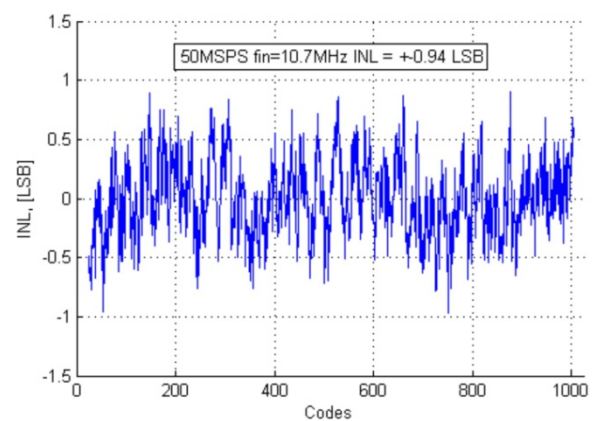


Figure 15: INL with $F_S= 50$ MSPS and $f_{in}= 10.7$ MHz

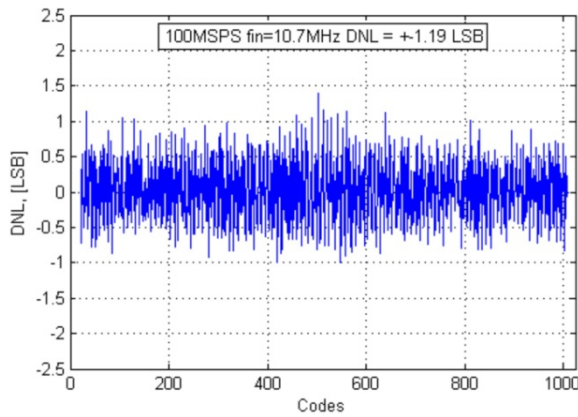


Figure 16: DNL with $F_S = 100$ MSPS and $f_{in} = 10.7$ MHz

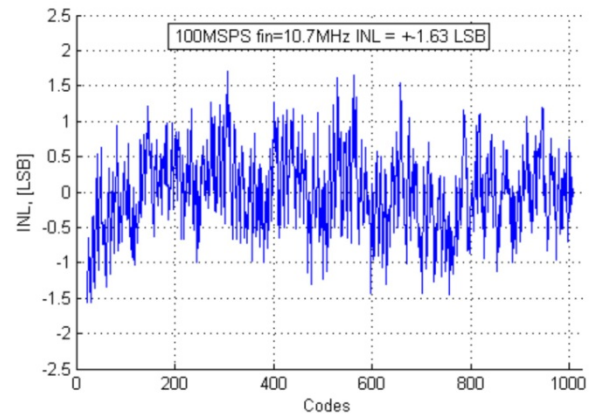


Figure 17: INL with $F_S = 100$ MSPS and $f_{in} = 10.7$ MHz

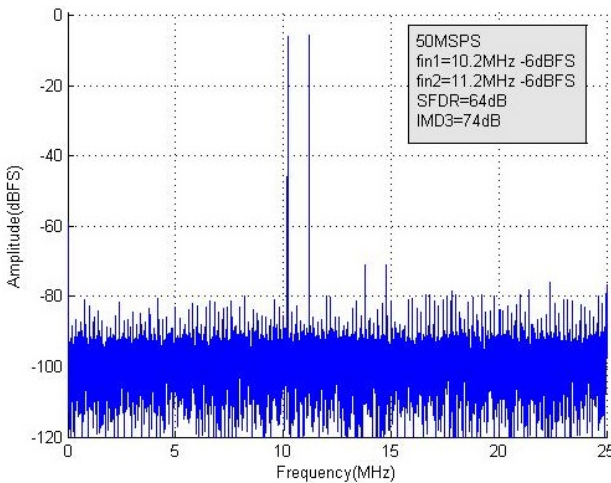


Figure 18: Spectrum with $F_S = 50$ MSPS, $f_{in1} = 10.2$ MHz and $f_{in2} = 11.2$ MHz

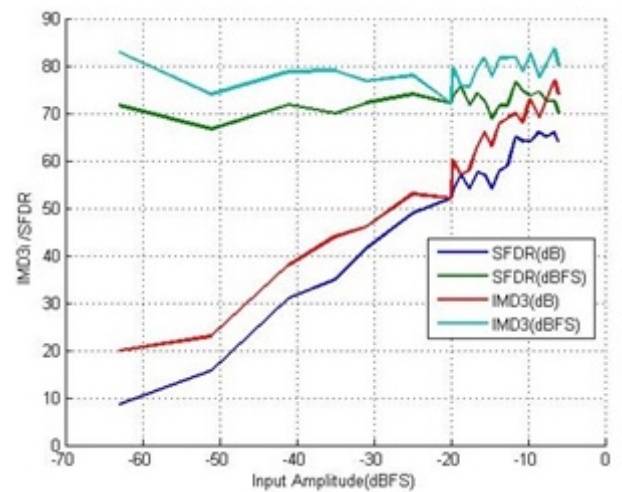


Figure 19: IMD3/SFDR vs. input amplitude with $F_S = 50$ MSPS, $f_{in1} = 10.2$ MHz and $f_{in2} = 11.2$ MHz

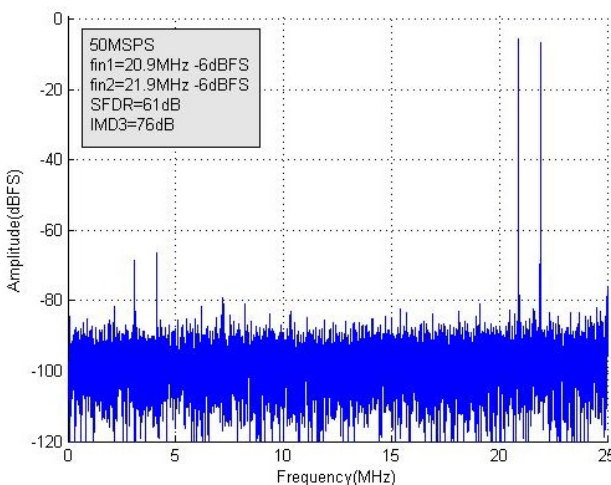


Figure 20: Spectrum with $F_S = 50$ MSPS, $f_{in1} = 20.9$ MHz and $f_{in2} = 21.9$ MHz

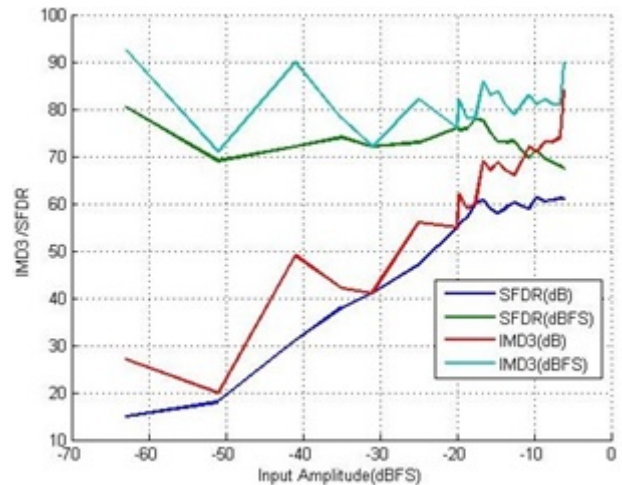


Figure 21: IMD3/SFDR vs. input amplitude with $F_S = 50$ MSPS, $f_{in1} = 20.9$ MHz and $f_{in2} = 21.9$ MHz

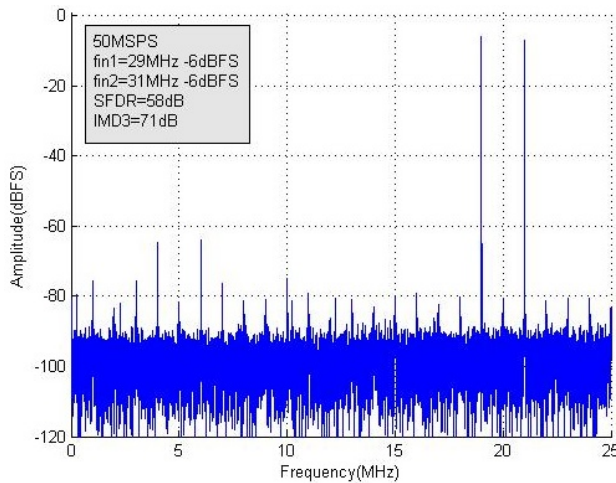


Figure 22: Spectrum with $F_S = 50$ MSPS, $f_{in1} = 29$ MHz and $f_{in2} = 31$ MHz

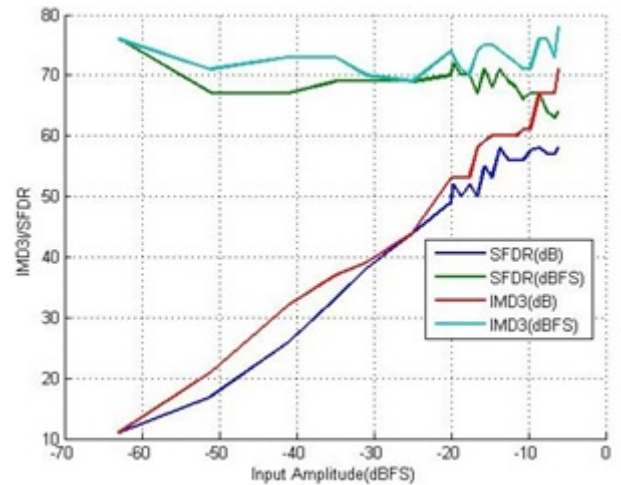


Figure 23: IMD3/SFDR vs. input amplitude with $F_S = 50$ MSPS, $f_{in1} = 29$ MHz and $f_{in2} = 31$ MHz

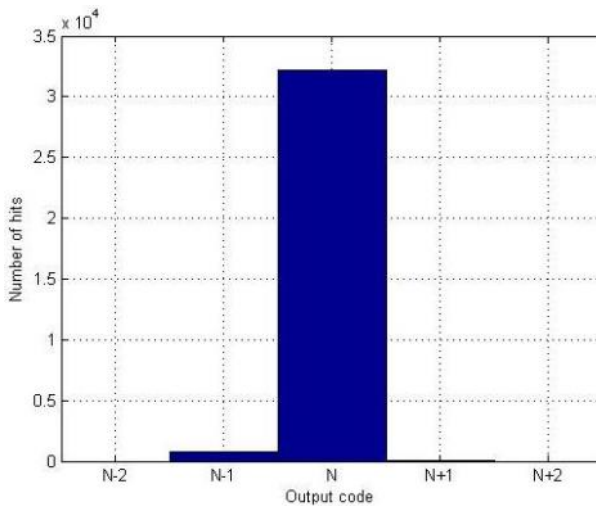


Figure 24: Input histogram $F_S = 50$ MSPS

12. DELIVERABLES

Depending on license type IP may include:

- Schematic or NetList
- Layout or blackbox
- Verilog, lef and lib files
- Extracted view (optional)
- GDSII
- DRC, LVS, antenna report
- Test bench with saved configurations (optional)
- Documentation

REVISION HISTORY

1. From version 1.0:
 - Section 3 was changed (refer to page 1)
 - Section 4 was changed (refer to page 2)
 - Section 5 was changed (refer to page 3)
 - Subsection 10.2 was changed (refer to page 5)
2. From version 1.1:
 - Section 1 was changed (refer to page 1)
 - Section 3 was changed (refer to page 1)
 - Section 4 was changed (refer to page 2)
 - Section 5 was changed (refer to page 3)
 - Section 6 shifted to section 8
 - Section 6 was added (refer to page 4)
 - Section 7 shifted to section 9
 - Section 7 was added (refer to page 4)
 - Section 8 was changed (refer to page 4)
 - Section 9 shifted to section 10
 - Section 9 was added (refer to page 6)
 - Subection 10.2 was changed (refer to page 7)